风光欣技术资料

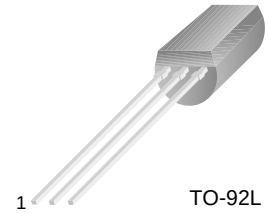
A1023

—PNP silicon —

■■**APPLICATION:** High Voltage Applications.

■■**MAXIMUM RATINGS**（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-120	V
Collector-emitter voltage	V_{CEO}	-120	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-800	mA
Collector Power Dissipation	P_C	1	W
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃



TO-92L

1. Emitter 2. Collector 3. Base

■■**ELECTRICAL CHARACTERISTICS**（**Ta=25℃**）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	80		240		V_{CE}= -5V，I_C= -100mA
Collector Cut-off Current	I_{CBO}			-0.1	μA	V_{CB}= -120V，I_E=0
Emitter Cut-off Current	I_{EBO}			-0.1	μA	V_{EB}= -5V，I_C=0
Collector-Base Breakdown Voltage	BV_{CBO}	-120			V	I_C= -1mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	-120			V	I_C= -10mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	-5			V	I_E= -1mA，I_C=0
Base-Emitter Voltage	V_{BE}			-1	V	V_{CE}= -5V，I_C= -500mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-1	V	I_C= -500mA，I_B= -50mA
Gain bandwidth product	f_T	50	120		MHz	I_C= -100mA，V_{CE}= -5V
Common Base Output Capacitance	C_{ob}			40	pF	V_{CB}= -10V，I_E=0，f = 1MHz

■■hFE **Classification**

Classification	O	Y
h_{FE}	80~160	120~240